



N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

| BV _{DSS} | R _{DS(ON)} Max | I _D Max T _C = +25°C |
|-------------------|--|--|
| | 3.2 m Ω @ V _{GS} = 10V | 100A |
| 30V | 5.2mΩ @ V _{GS} = 4.5V | 80A |

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

PowerDI5060-8

- Backlighting
- Power Management Functions
- **DC-DC Converters**

Features and Benefits

- Low R_{DS(ON)} Minimizes On-State Losses
- Excellent Q_{gd} x R_{DS(ON)} Product (FOM)
- Advanced Technology for DC-DC Converters
- Small Form Factor Thermally Efficient Package Enables Higher **Density End Products**
- 100% Unclamped Inductive Switching Ensures More Reliability
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

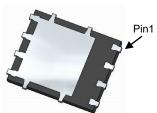
Mechanical Data

- Case: PowerDI[®]5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.097 grams (Approximate)

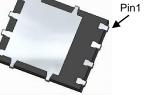


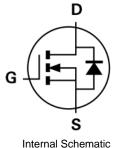


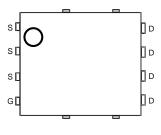
Notes:



Bottom View







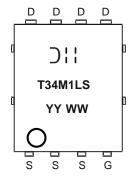
Top View Pin Configuration

Ordering Information (Note 4)

| Part Number | Case | Packaging |
|---------------|---------------|-------------------|
| DMT34M1LPS-13 | PowerDI5060-8 | 2,500/Tape & Reel |

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
 - 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 - 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



⊃¦¦= Manufacturer's Marking T34M1LS = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 17 = 2017) WW = Week (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

| Characteristic | | Symbol | Value | Unit |
|---|----------------------------------|----------------|-----------|------|
| Drain-Source Voltage | V_{DSS} | 30 | V | |
| Gate-Source Voltage | V_{GSS} | ±20 | V | |
| Continuous Drain Current, V _{GS} = 10V (Note 6) | $T_A = +25$ °C $T_A = +70$ °C | I _D | 21 17 | Α |
| Continuous Drain Current, $V_{GS} = 10V$ (Note 7) $ T_C = +25^{\circ}C $ $ T_C = +70^{\circ}C $ | | I _D | 100 80 | Α |
| Maximum Continuous Body Diode Forward Current (Note 6) | I _S | 3 | А | |
| Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%) | I _{DM} | 250 | Α | |
| Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle | I _{SM} | 250 | Α | |
| Avalanche Current, L=0.1mH (Note 8) | I _{AS} | 38.5 | Α | |
| Avalanche Energy, L=0.1mH (Note 8) | E _{AS} | 78 | mJ | |

Thermal Characteristics

| Characteristic | | Symbol | Value | Unit |
|--|------------------------|--------------------|-------------|------|
| Total Power Dissipation (Note 5) | $T_A = +25^{\circ}C$ | P_{D} | 1.3 | W |
| Thermal Resistance, Junction to Ambient (Note 5) | Steady State | $R_{\theta JA}$ | 98 | °C/W |
| Total Power Dissipation (Note 6) | T _A = +25°C | P _D | 2.2 | W |
| Thermal Resistance, Junction to Ambient (Note 6) | Steady State | $R_{\theta JA}$ | 58 | °C/W |
| Total Power Dissipation (Note 7) | T _C = +25°C | P _D | 42 | W |
| Thermal Resistance, Junction to Case (Note 7) | | $R_{\theta JC}$ | 2.5 | °C/W |
| Operating and Storage Temperature Range | | $T_{J_{I}}T_{STG}$ | -55 to +150 | °C |

Electrical Characteristics (T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Min | Тур | Max | Unit | Test Condition |
|--|---------------------|-----|------|------|------|---|
| OFF CHARACTERISTICS (Note 9) | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | 30 | _ | _ | V | $V_{GS} = 0V, I_D = 250\mu A$ |
| Zero Gate Voltage Drain Current | I _{DSS} | _ | _ | 1 | μΑ | V _{DS} = 24V, V _{GS} = 0V |
| Gate-Source Leakage | I _{GSS} | _ | _ | ±100 | nA | $V_{GS} = 20V, V_{DS} = 0V$ $V_{GS} = -16V, V_{DS} = 0V$ |
| ON CHARACTERISTICS (Note 9) | | | • | • | • | |
| Gate Threshold Voltage | V _{GS(TH)} | 1.0 | _ | 3.0 | V | $V_{DS} = V_{GS}, I_{D} = 250 \mu A$ |
| Static Drain-Source On-Resistance | В | _ | 2.6 | 3.2 | mΩ | $V_{GS} = 10V, I_D = 20A$ |
| Static Drain-Source On-Resistance | R _{DS(ON)} | _ | 3.7 | 5.2 | | $V_{GS} = 4.5V, I_D = 20A$ |
| Diode Forward Voltage | V _{SD} | _ | 0.7 | 1.2 | V | $V_{GS} = 0V$, $I_S = 2A$ |
| DYNAMIC CHARACTERISTICS (Note 10) | | | | | | |
| Input Capacitance | C _{iss} | _ | 2242 | _ | | V _{DS} = 15V, V _{GS} = 0V, f = 1.0MHz |
| Output Capacitance | Coss | _ | 960 | _ | pF | |
| Reverse Transfer Capacitance | C _{rss} | _ | 217 | _ | | |
| Gate Resistance | Rg | _ | 1.0 | _ | Ω | $V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$ |
| Total Gate Charge (V _{GS} = 10V) | Qg | _ | 39 | _ | | |
| Total Gate Charge (V _{GS} = 4.5V) | Qg | _ | 20 | _ | ~^ | V 45V L 20A |
| Gate-Source Charge | Qgs | _ | 5.6 | _ | nC | V _{DD} = 15V, I _D = 20A |
| Gate-Drain Charge | Q _{gd} | _ | 7.0 | _ | | |
| Turn-On Delay Time | t _{D(ON)} | _ | 5.6 | _ | | $V_{DD} = 15V, V_{GS} = 10V,$ $R_g = 3\Omega, I_D = 20A$ |
| Turn-On Rise Time | t _R | _ | 13.8 | _ | | |
| Turn-Off Delay Time | t _{D(OFF)} | _ | 22.4 | _ | ns | |
| Turn-Off Fall Time | t _F | _ | 11.4 | _ | | |
| Reverse Recovery Time | t _{RR} | _ | 22 | _ | ns | I _F = 15A, dI/dt = 500A/μs |
| Reverse Recovery Charge | Q _{RR} | _ | 27 | _ | nC | I _F = 15A, dI/dt = 500A/μs |

Notes: 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.

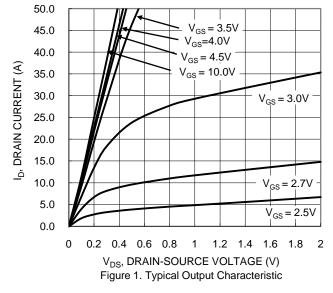
^{6.} Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
7. Thermal resistance from junction to soldering point (on the exposed drain pad).

^{8.} I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_J = +25$ °C.

^{9.} Short duration pulse test used to minimize self-heating effect.

^{10.} Guaranteed by design. Not subject to product testing.





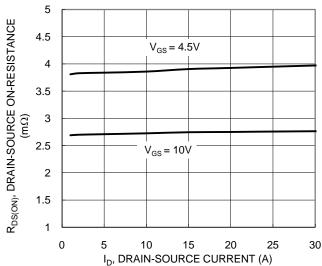


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

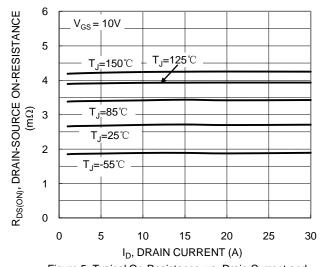
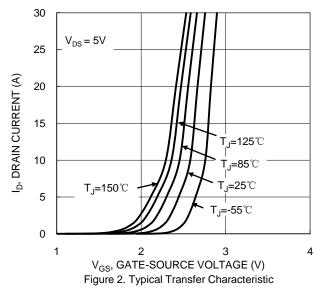


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature



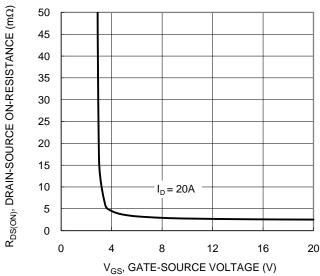


Figure 4. Typical Transfer Characteristic

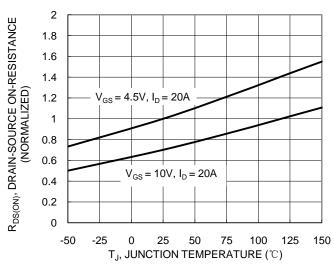


Figure 6. On-Resistance Variation with Junction Temperature





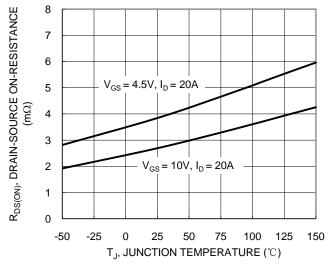


Figure 7. On-Resistance Variation with Junction Temperature

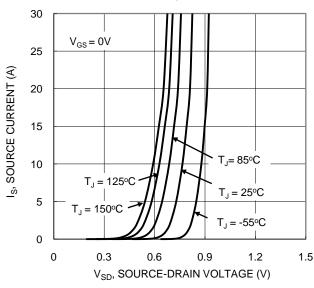
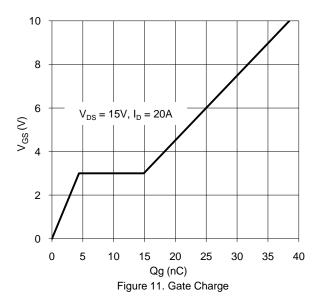


Figure 9. Diode Forward Voltage vs. Current



3 $V_{GS(TH)},$ GATE THRESHOLD VOLTAGE (V) 2.5 2 $I_D = 1 \text{mA}$ 1.5 $I_{D} = 250 \mu A$ 1 0.5 0 -25 -50 75 100 125 0 25 50 150 T_J , JUNCTION TEMPERATURE ($^{\circ}$ C)

Figure 8. Gate Threshold Variation vs. Junction Temperature

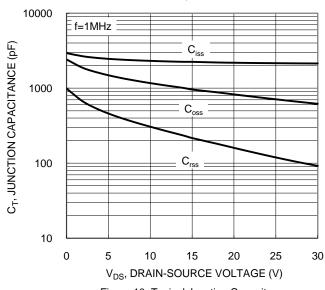
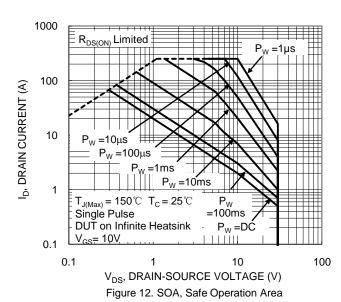


Figure 10. Typical Junction Capacitance





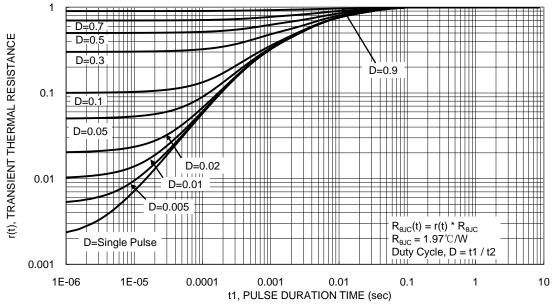


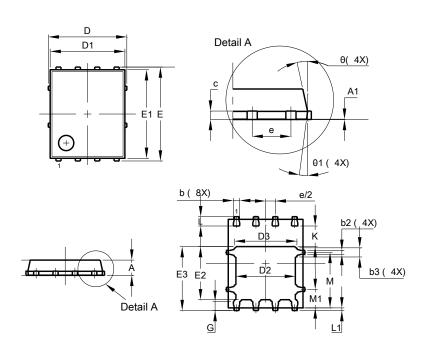
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8

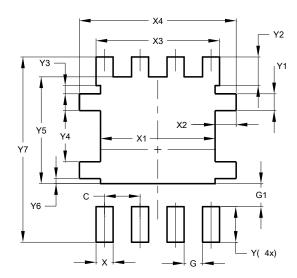


| PowerDI5060-8 | | | | |
|----------------------|----------------|-------|-------|--|
| Dim | Min | Max | Тур | |
| Α | 0.90 | 1.10 | 1.00 | |
| A1 | 0.00 | 0.05 | - | |
| b | 0.33 | 0.51 | 0.41 | |
| b2 | 0.200 | 0.350 | 0.273 | |
| b3 | 0.40 | 0.80 | 0.60 | |
| С | 0.230 | 0.330 | 0.277 | |
| D | 5.15 BSC | | | |
| D1 | 4.70 | 5.10 | 4.90 | |
| D2 | 3.70 | 4.10 | 3.90 | |
| D3 | 3.90 4.30 4.10 | | 4.10 | |
| Е | 6.15 BSC | | | |
| E1 | 5.60 | 6.00 | 5.80 | |
| E2 | 3.28 | 3.68 | 3.48 | |
| E3 | 3.99 | 4.39 | 4.19 | |
| е | 1.27 BSC | | | |
| G | 0.51 | 0.71 | 0.61 | |
| K | 0.51 | - | - | |
| L | 0.51 | 0.71 | 0.61 | |
| L1 | 0.100 | 0.200 | 0.175 | |
| M | 3.235 | 4.035 | 3.635 | |
| M1 | 1.00 | 1.40 | 1.21 | |
| Θ | 10° | 12° | 11° | |
| Θ1 | 6° | 8° | 7° | |
| All Dimensions in mm | | | | |

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8



| Dimensions | Value (in mm) | | |
|------------|---------------|--|--|
| С | 1.270 | | |
| G | 0.660 | | |
| G1 | 0.820 | | |
| X | 0.610 | | |
| X1 | 4.100 | | |
| X2 | 0.755 | | |
| Х3 | 4.420 | | |
| X4 | 5.610 | | |
| Υ | 1.270 | | |
| Y1 | 0.600 | | |
| Y2 | 1.020 | | |
| Y3 | 0.295 | | |
| Y4 | 1.825 | | |
| Y5 | 3.810 | | |
| Y6 | 0.180 | | |
| Y7 | 6.610 | | |



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